

L Number	Hits	Search Text	DB	Time stamp
5	48	(contact adj hole) with (selectively) with TiN	USPAT; US-PGPUB	2004/07/15 10:56
6	31	((contact adj hole) with (selectively) with TiN) and @ad<20020204	USPAT; US-PGPUB	2004/07/15 10:57
7	10	(contact adj hole) with (selectively or selective) with (deposition or depositing) with TiN	USPAT; US-PGPUB	2004/07/15 10:59
8	6	((contact adj hole) with (selectively or selective) with (deposition or depositing) with TiN) and @ad<20020204	USPAT; US-PGPUB	2004/07/15 10:59
9	94	((selectively or selective) with (deposition or depositing) with TiN) and (barrier with TiN)	USPAT; US-PGPUB	2004/07/15 10:59
10	71	((selectively or selective) with (deposition or depositing) with TiN) and (barrier with TiN)) and @ad<20020204	USPAT; US-PGPUB	2004/07/15 11:00

US-PAT-NO: 5821164

DOCUMENT-IDENTIFIER: US 5821164 A

TITLE: Method for forming metal line

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Application Filing Date - AD (1):

19960913

Detailed Description Text - DETX (14):

As illustrated in FIG. 2f, a material among Al, Cu, Ti, and TiN is selectively deposited on the exposed surface of the interlevel layer 14a including the contact hole 15, to form a conductive layer 16.

Detailed Description Text - DETX (29):

As illustrated in FIG. 3f, a material among Al, Cu, Ti and TiN is selectively deposited on the exposed surface of the first and second interlevel layers 24 and 25a including the contact hole 26, to form a conductive layer 27.

Detailed Description Text - DETX (48):

As illustrated in FIG. 4g, a material among Al, Cu, Ti and TiN is selectively deposited on the exposed surface of the interlevel layer 35a including the contact hole 36 to form a second conductive layer 37.